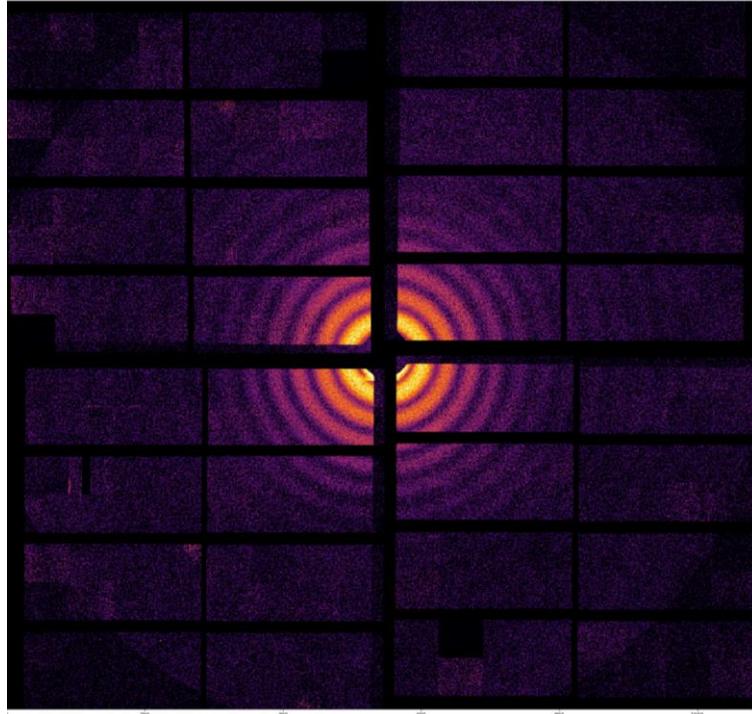
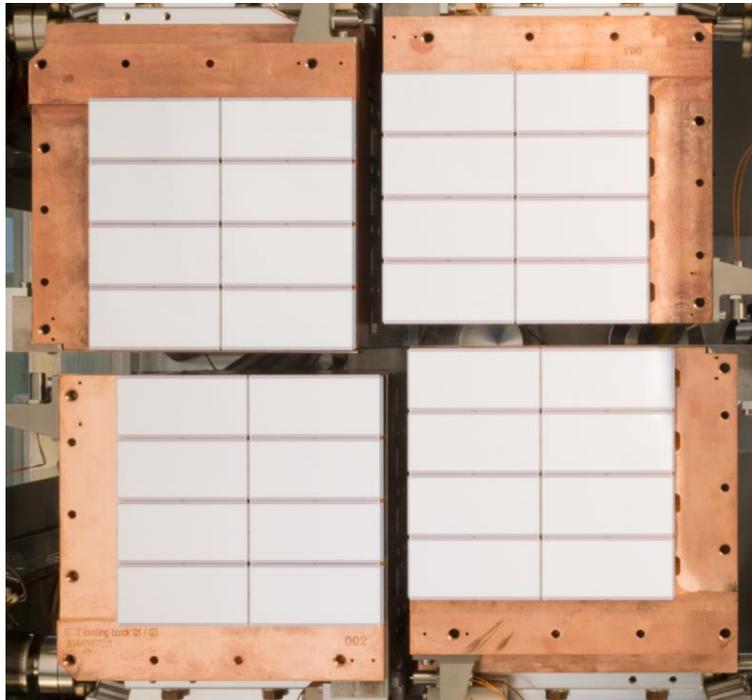


# The DSSC soft X-ray Detectors with Mega-frame Readout Capability for the European XFEL

Stefano Maffessanti on behalf of the DSSC Collaboration



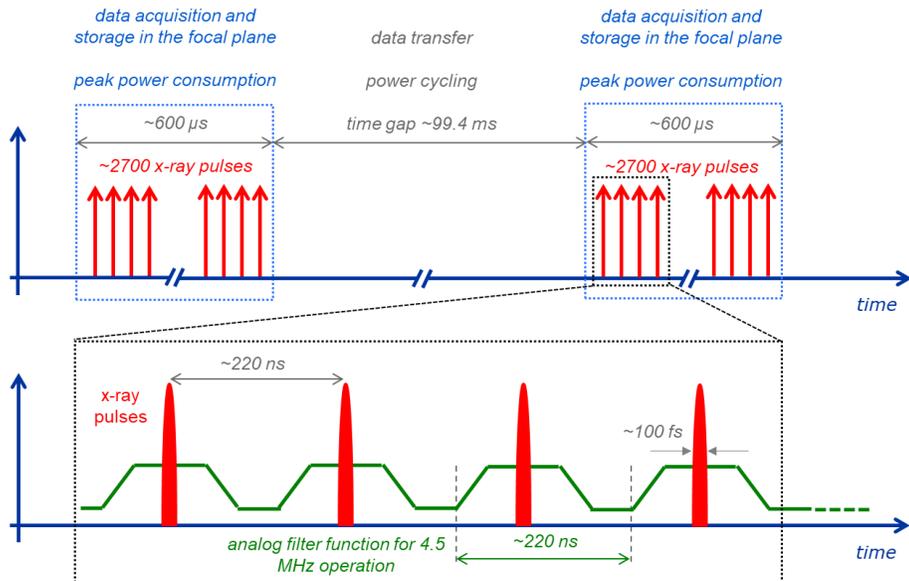
15th Pisa Meeting on Advanced Detectors

Photo Detectors and Particle ID

M. Porro<sup>1</sup>, L. Andricek<sup>2</sup>, S. Aschauer<sup>3</sup>, A. Castoldi<sup>4,5</sup>, M. Donato<sup>1</sup>, J. Engelke<sup>1</sup>, F. Erdinger<sup>7</sup>, C. Fiorini<sup>4,5</sup>, P. Fischer<sup>7</sup>, H. Graafsma<sup>8</sup>, A. Grande<sup>4</sup>, C. Guazzoni<sup>4,5</sup>, K. Hansen<sup>8</sup>, S. Hauf, P. Kalavakuru<sup>8</sup>, H. Klaer<sup>9</sup>, M. Kirchgessner<sup>7</sup>, A. Kugel<sup>7</sup>, M. Kuster<sup>1</sup>, P. Lechner<sup>2</sup>, D. Lomidze<sup>1</sup>, S. Maffessanti<sup>8</sup>, M. Manghisoni<sup>6</sup>, S. Nidhi<sup>7</sup>, V. Re<sup>6</sup>, C. Reckleben<sup>9</sup>, E. Riceputi<sup>6</sup>, R. Richter<sup>2</sup>, A. Samartsev<sup>1</sup>, J. Soldat<sup>8</sup>, L. Strueder<sup>3</sup>, M. Turcato<sup>1</sup>, G. Weidenspointner<sup>1</sup>, C. Wunderer<sup>8</sup>

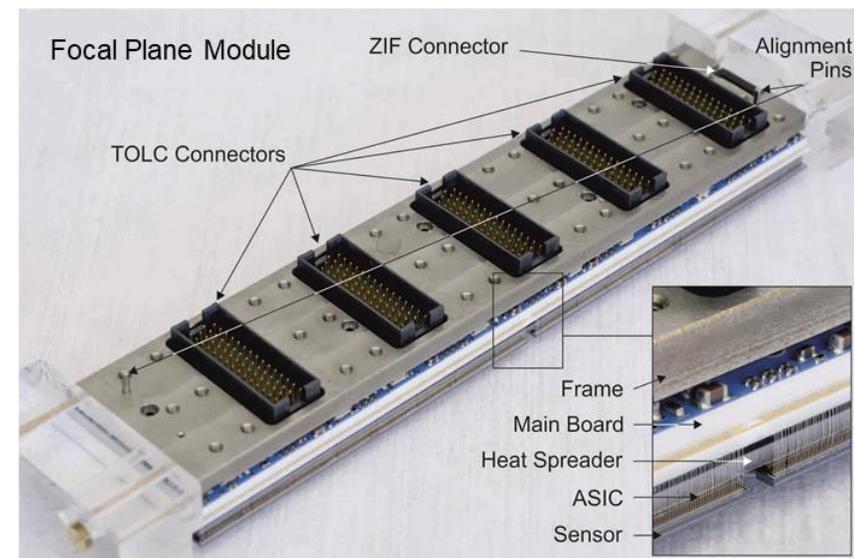
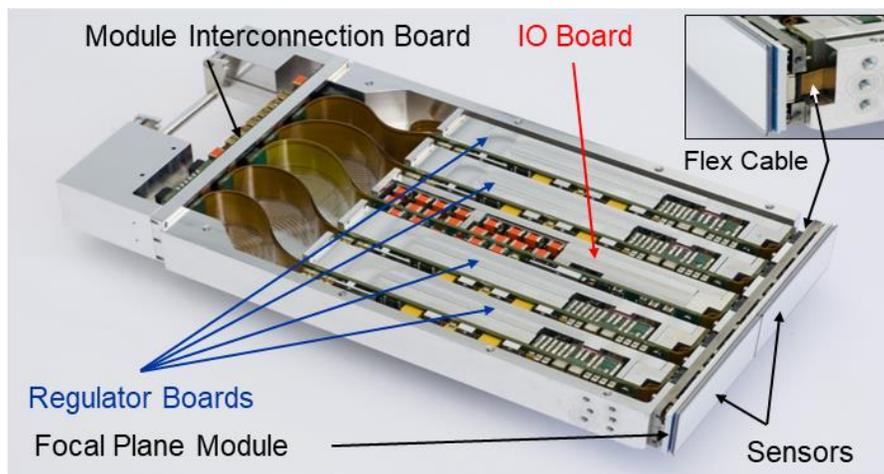
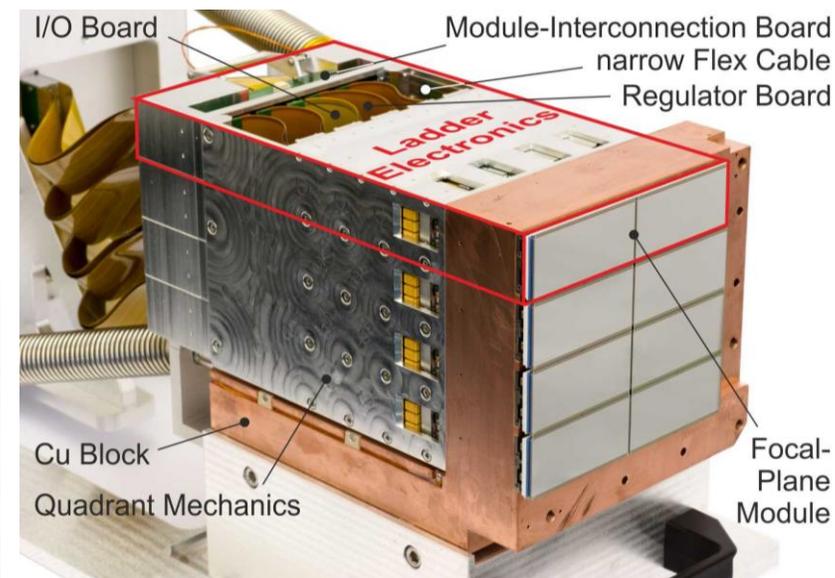
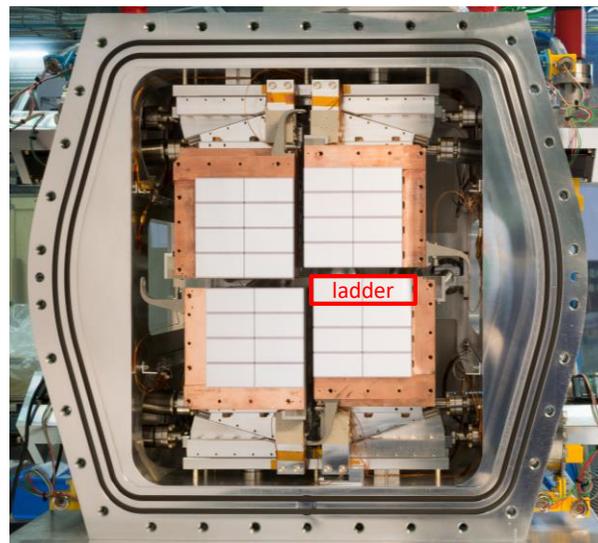
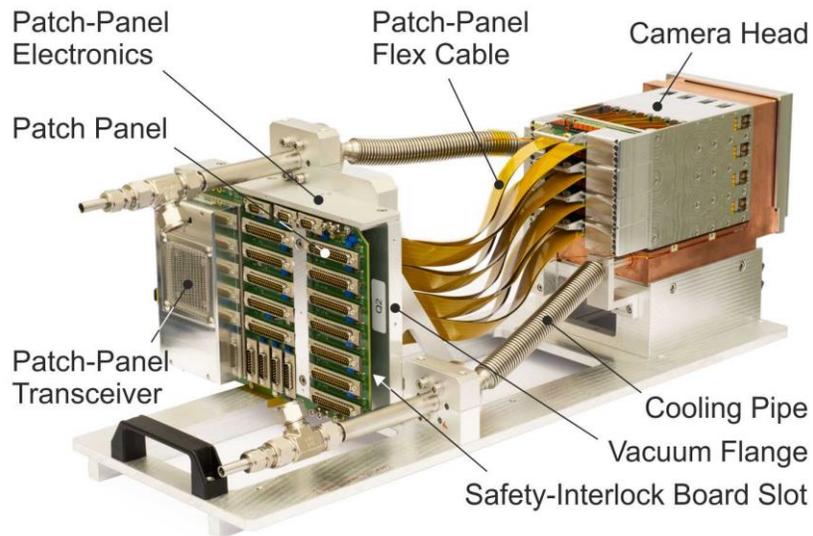
- 1) European XFEL GmbH, Schenefeld, Germany
- 2) MPG Halbleiterlabor, Muenchen, Germany
- 3) PNSensor GmbH, Muenchen, Germany
- 4) Dipartimento di Elettronica e Informazione, Politecnico di Milano, Milano, Italy
- 5) Sezione di Milano, Italian National Institute of Nuclear Physics (INFN), Milano, Italy
- 6) Dipartimento di ingegneria industriale, Università di Bergamo, Bergamo, Italy
- 7) Zentrales Institut für Technische Informatik, Universitaet Heidelberg, Heidelberg, Germany
- 8) Deutsches Elektronen-Synchrotron DESY, Hamburg, Germany

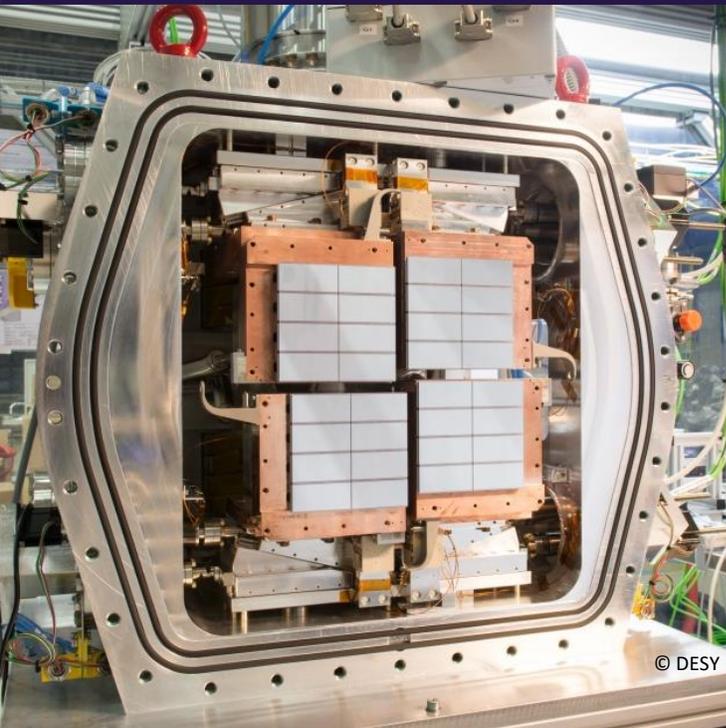




Parameter		Value
Target energy range		0.25 keV – 6 keV
Pixel count		1024 × 1024
Pixel shape		hexagonal
Sensor pixel pitch		~204 μm × 236 μm
Active area		~ 21 cm × 21 cm
Input photon range / pixel / pulse (*)	MiniSDD	2 <sup>n</sup> × N - 1
	DEPFET	> 10 <sup>4</sup>
Achievable noise	MiniSDD	~ 60 e- r.m.s.
	DEPFET	~ 10 e- r.m.s.
Peak frame rate		4.5 MHz
Stored frames per X-ray train		800
Average / peak data rate		134/ 144 Gbit / s
Average power consumption		~ 260 W
Operating temperature		-20° C optimum, room T possible

- 1 Megapixel camera **4.5 MHz peak frame rate**
  - 4 quadrants (512 x 512)
  - **16 ladders (512 x 128)**
  - 32 monolithic sensors 128x256
  - 256 Readout ASICs 64 x64
  
- Sensors:
  - **MiniSDD arrays 1<sup>st</sup> camera**
  - **DEPFET arrays 2<sup>nd</sup> camera**
  
- Readout concept
  - **Full parallel readout**
  - In pixel analog to digital conversion
  - **In pixel digital storage** (800 frames) with the possibility to overwrite non-valid frames (VETO)
  - Output average **data rate: 134.4 Gbit/s**



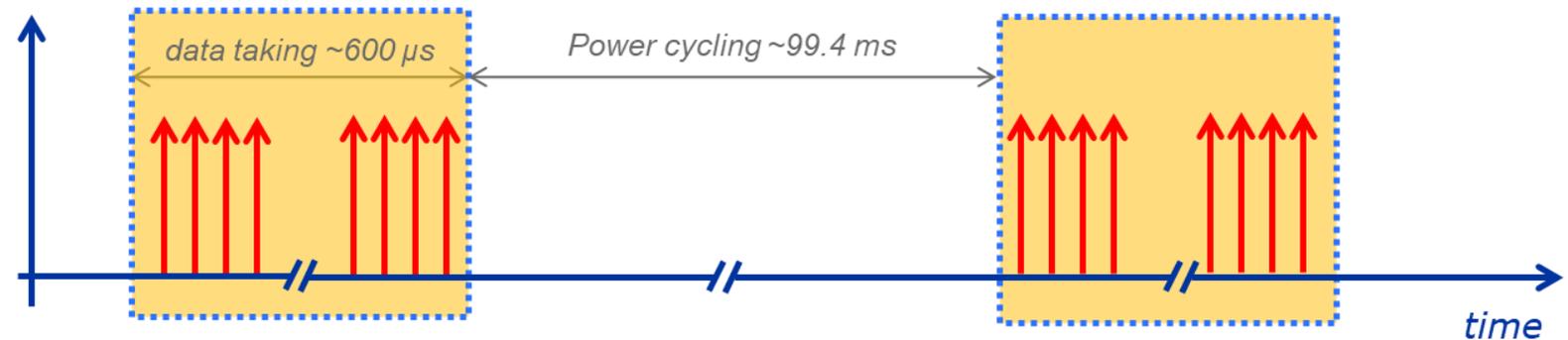


		Q1	Q2	Q3	Q4	Camera	
Quadrant	IOB	12,42	12,44	12,38	12,21	49,45	
	RB	9,42	9,05	9,21	8,99	36,66	
	FPM	MB	10,09	10,07	10,07	10,07	40,31
		ASIC	5,30	4,98	5,12	4,84	20,25
Sensor		0,60	0,61	0,61	0,52	2,35	
Periphery	PP	2,65	2,54	2,61	2,56	10,36	
	PPT	24,71	24,42	24,36	24,34	97,82	
	SIB	1,41	1,35	1,34	1,37	5,47	
TOTAL		66,62	65,45	65,69	64,90	262,66	

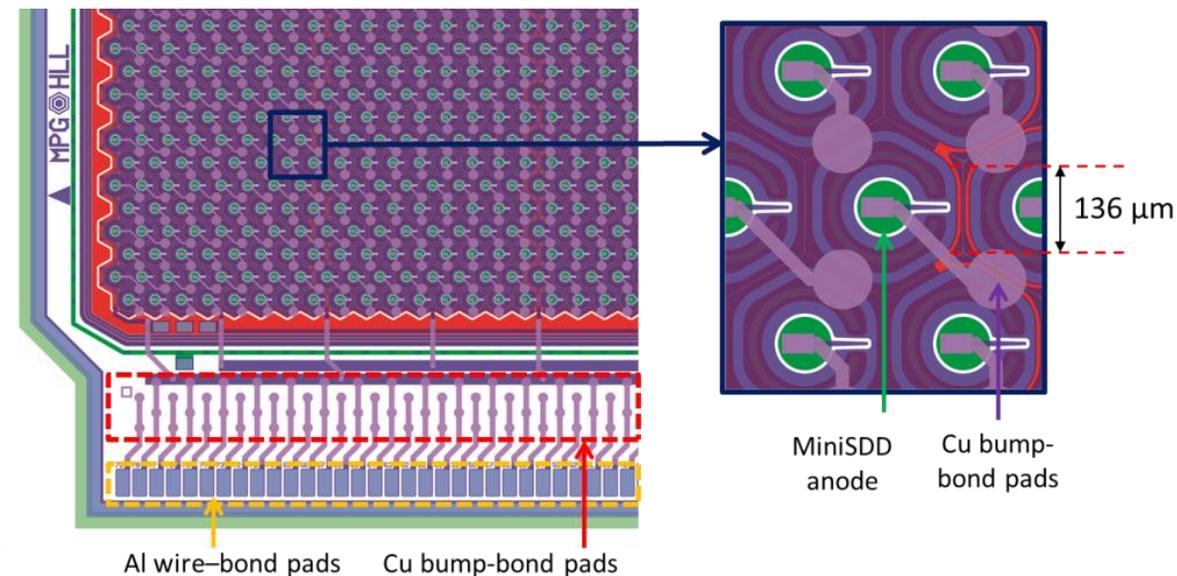
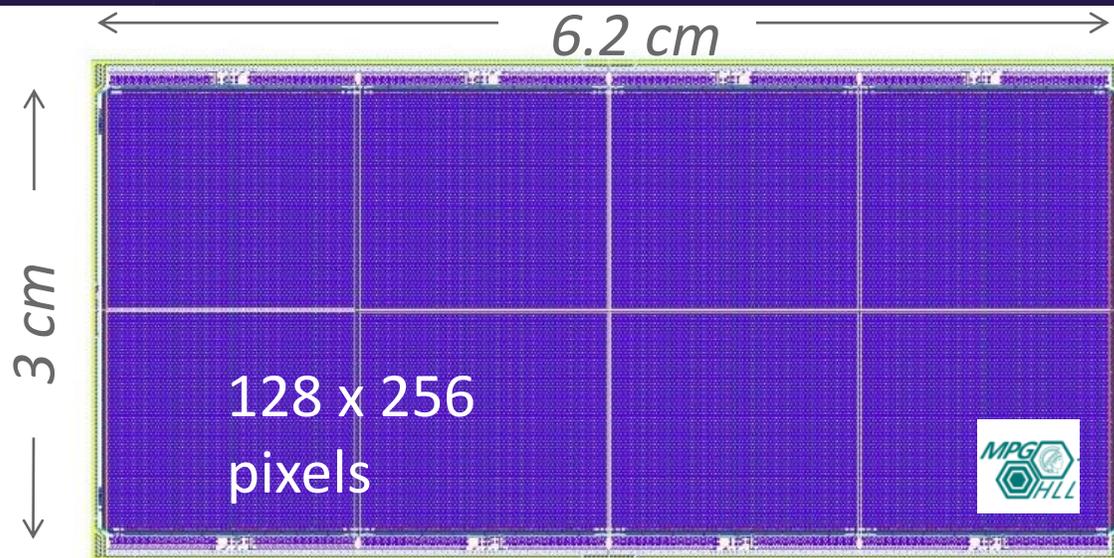
**Ladder Electronics:**  
86 W (33%)

**Focal Plane:**  
63 W (24%)

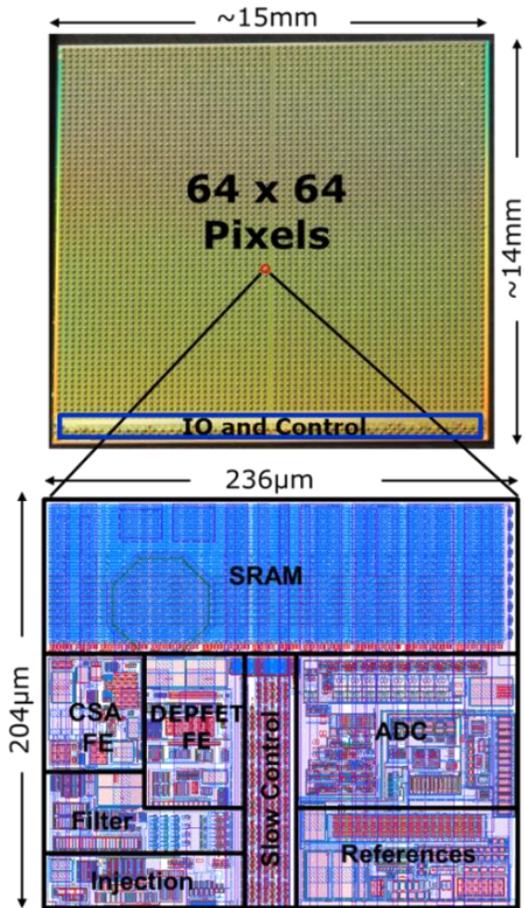
**Periphery:**  
114 W (43%)



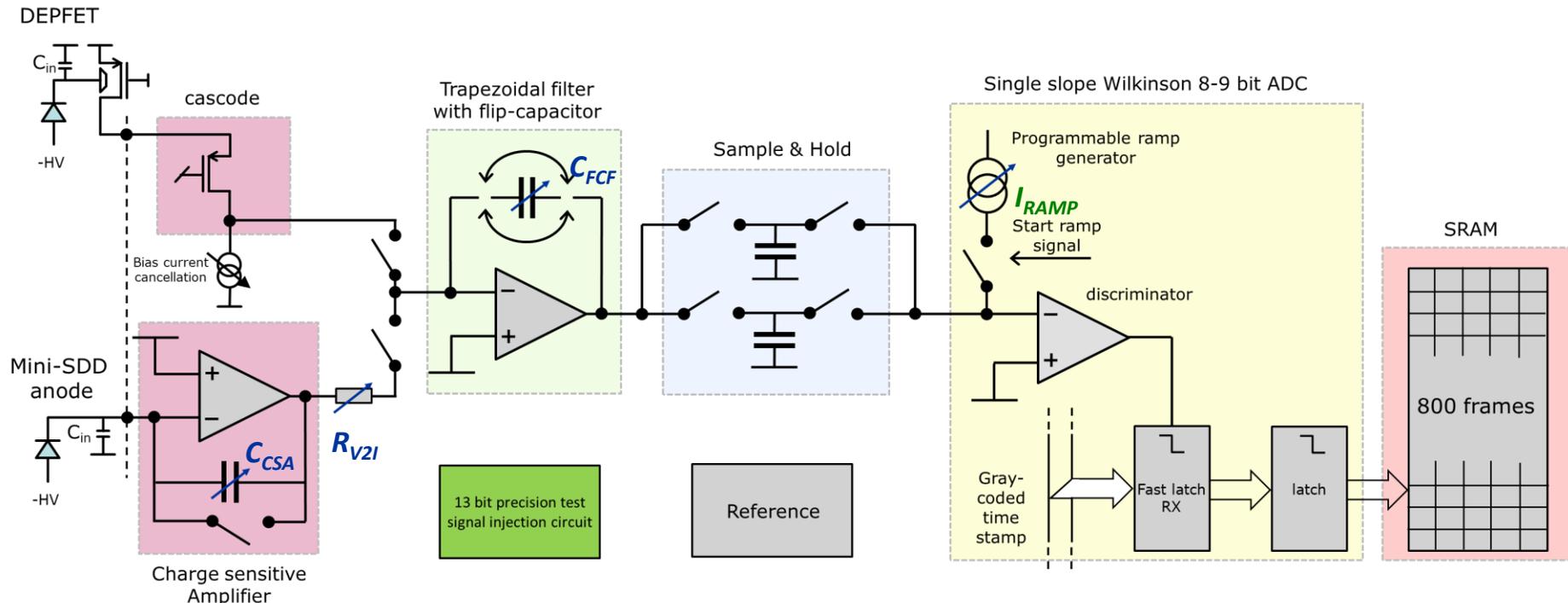
- Power Cycling: total Power Dissipation 263 W (250 μW per Pixel)
- Coolant Load in Vacuum 149 W (142 μW per Pixel)
- In Agreement with Calculations & Expectations



- Large area monolithic **Mini Silicon Drift Detector** Arrays produced at the Semiconductor Laboratory of the Max Planck Society
  - 128 x 256 hexagonal pixels; hexagon side  $136\ \mu\text{m}$ ; pixel pitches  $204 \times 236\ \mu\text{m}$
  - passive collecting anode
  - 1 Alu layer, Cu layer
- Every pixel is bumped to the input of one CSA on the readout ASIC
  - **the system is linear**
  - Energy range and dynamic range are given by the gain of the ASIC and the ADC resolution (8 bit)



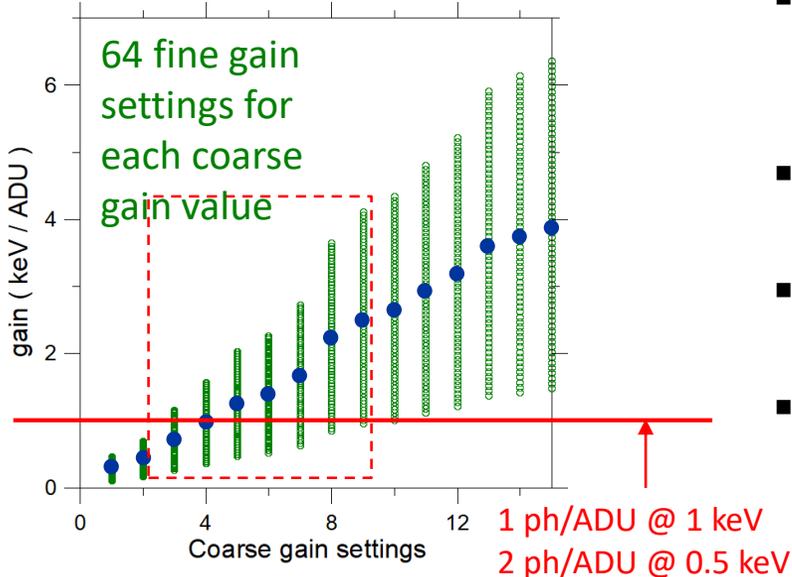
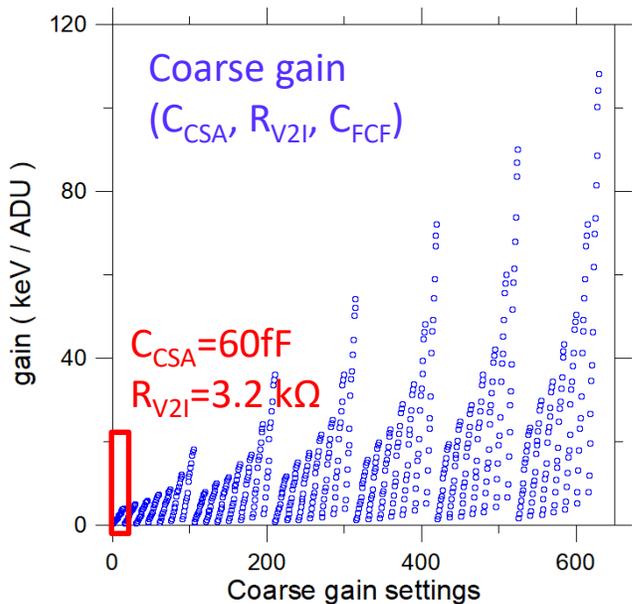
130 nm CMOS Process with C4 bumps



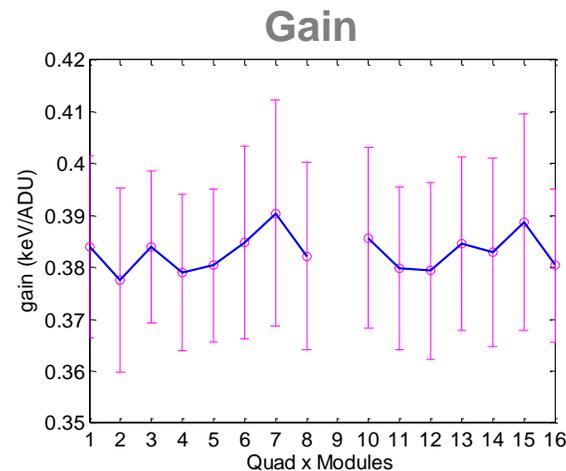
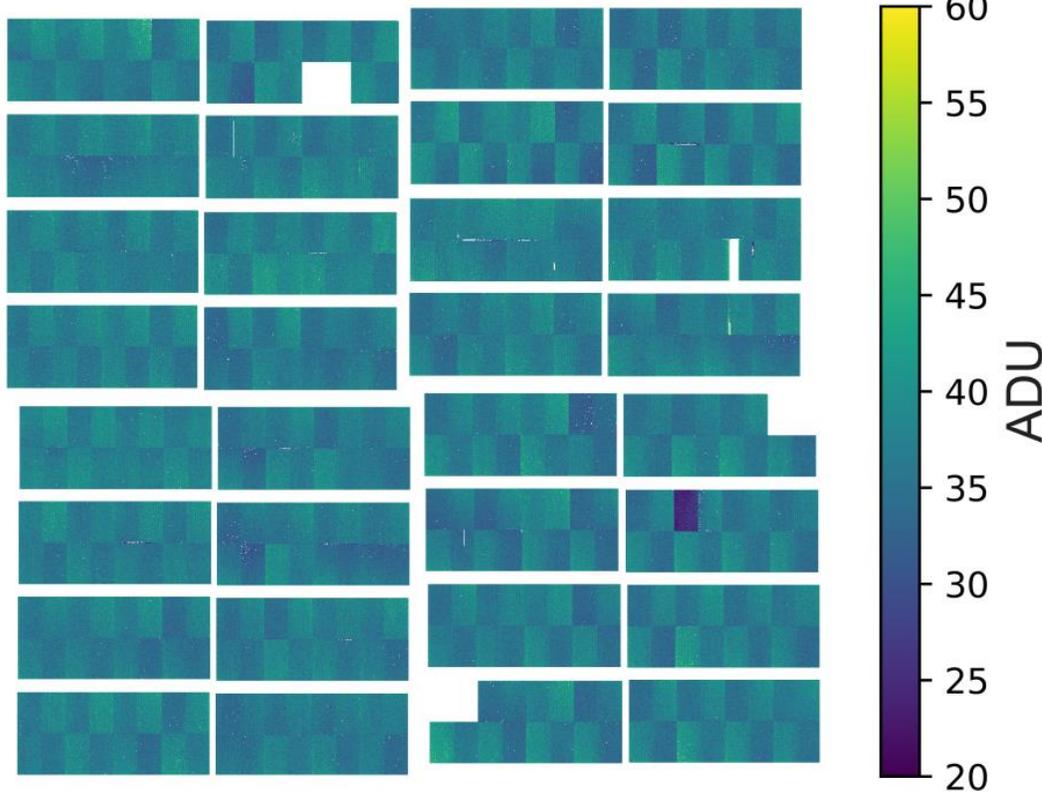
- Gain and offset can be adjusted pixel-wise:
  - **11 bits of coarse gain setting** for ph. energy and input range selection
  - **6 bits of gain fine trimming** (nominal accuracy 2%)
  - 4 bits for offset trimming (1.5 LSB range with 8% of granularity)

Pixel-wise coarse gain parameters      Pixel-wise fine gain trimming

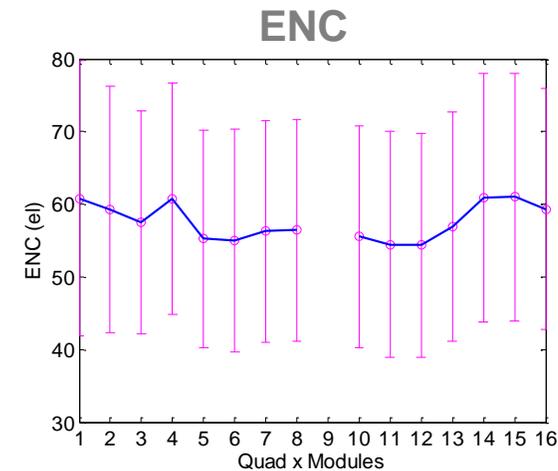
$$\frac{\text{keV}}{\text{ADU}} \propto \underbrace{C_{CSA} \cdot R_{V2I} \cdot C_{FCF}}_{\text{Pixel-wise coarse gain parameters}} \cdot \frac{1}{t_{filt}} \cdot \frac{1}{C_{S\&H}} \cdot \underbrace{I_{ramp}}_{\text{Pixel-wise fine gain trimming}} \cdot \frac{1}{2 \cdot f_{clock}}$$



- pixel-wise **coarse gain settings** make it possible
  - to operate with photons of **different energies**
  - to **define the input dynamic range**, associating a defined number of photons to a single ADU
  
- Pixel wise **fine-gain trimming** is needed
  - To equalize the gain dispersion over the pixels of the matrix
  - To have a precise association of number of photons and ADUs
  
- Pixel-wise **offset trimming** is needed to place the signal produced by one photon in the middle of one ADU (minimization of error count rate)
  
- It is possible to set **different gains in different regions** of the detector
  
- The overall gain settings are **overlapping and have a granularity <1%**
  
- Possible to define precisely the gain for any arbitrary energy for  $0.5 \text{ keV} \leq E_{\text{ph}} \leq 10 \text{ keV}$



average:  $382.9 \pm 3.6$  (1.0%)  
 average  $\sigma$ : 17.3 (4.5%)



average:  $57.6 \pm 2.5$  (4.4%)  
 average  $\sigma$ : 16.1 (27.9%)

- Failure Rate: 3 ASICs out of 256 are concerned (< 2 %)
- Camera calibration @XFEL with pulsed X-ray source PulXar
- Average gain  $\sim 400$  eV/ADU (un-trimmed) and ENC  $\sim 58$  e- @ 4.5 MHz
- Good uniformity for the 16 ladders

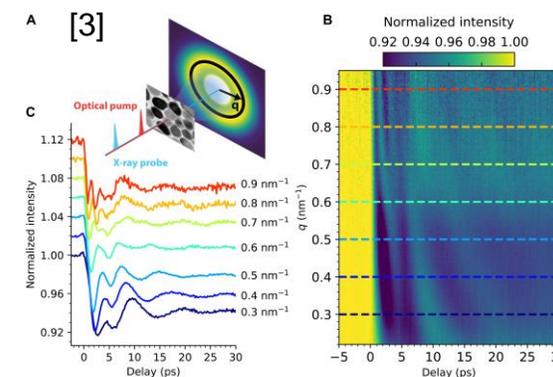
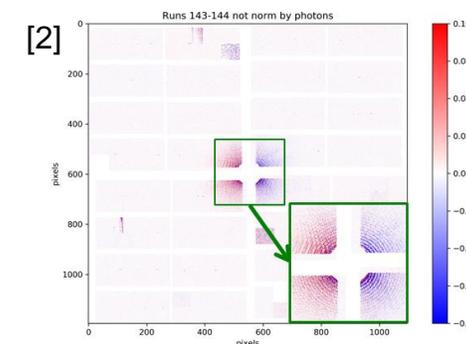
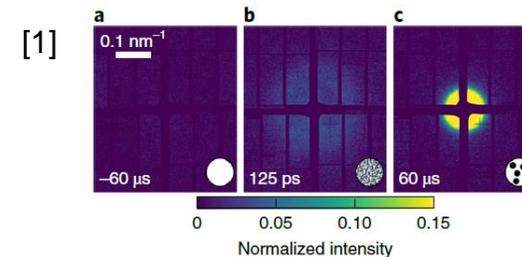
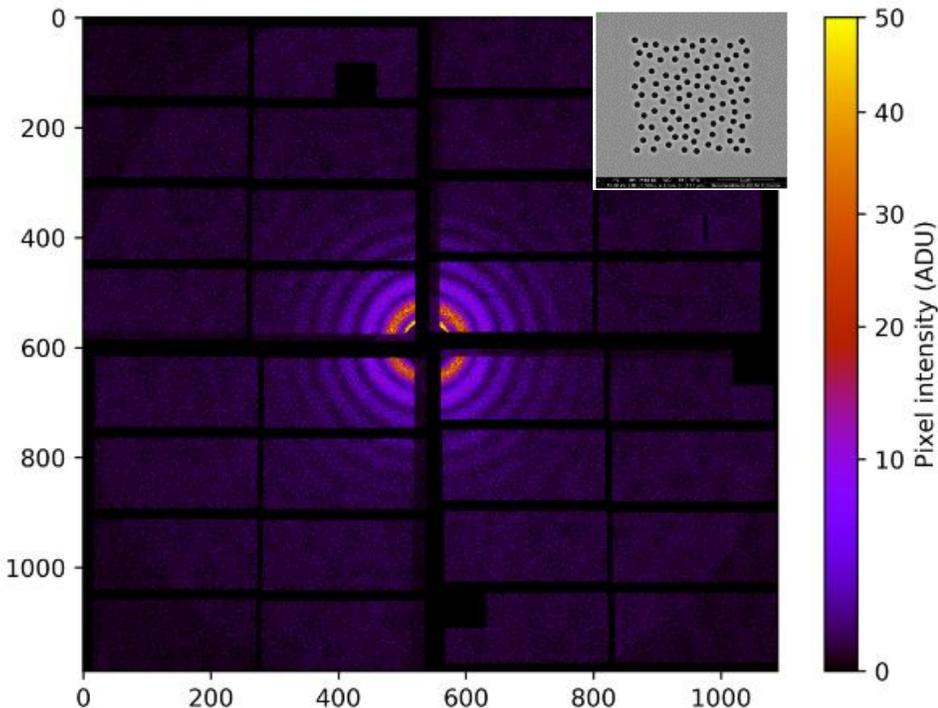


### Dark-Image Test

- w/o active Cooling at RT
- default Gain/Offset Settings

- Installation in May 2019 @ Spectroscopy and Coherent Scattering (SCS) Instrument
- First user experiment May 28, 2019
- Since installation (to Dec 2021):
  - ✓ **16** user experiments at SCS:
    - 8 Time resolved scattering
    - 7 Time resolved XAS
    - 1 Time resolved Holography
  - ✓ DSSC commissioned and installed at Small Quantum Systems (SQS) Instrument

Diffraction image of pinholes with 707 eV photons  
SCS commissioning



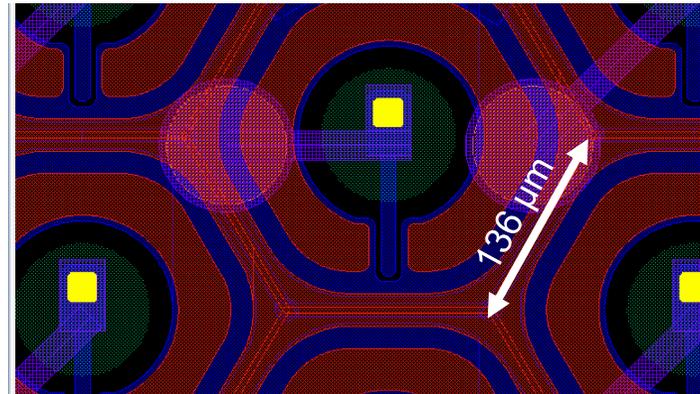
[1] Büttner, F; *et al.* Observation of fluctuation-mediated picosecond nucleation of a topological phase. *Nat. Mater.* **20**, 30–37 (2021). doi:10.1038/s41563-020-00807-1

[2] Hagström, N. Z.; *et al.* Megahertz-rate Ultrafast X-ray Scattering and Holographic Imaging at the European XFEL. *arXiv* (2022). doi:10.48550/arXiv.2201.06350

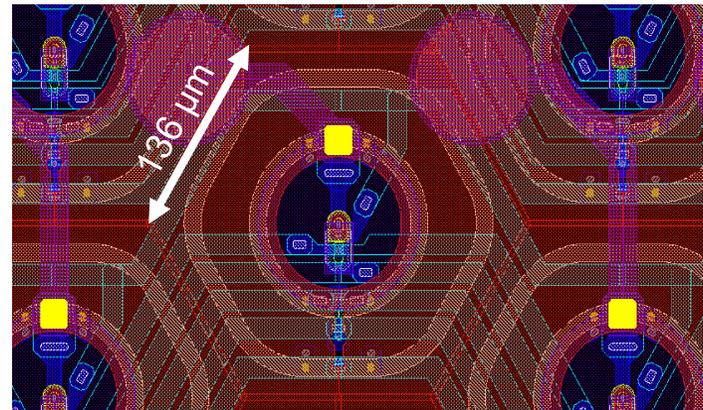
[3] Turenne, D.; *et al.* Nonequilibrium Sub-10 Nm Spin-Wave Soliton Formation in FePt Nanoparticles. *Sci. Adv.* 2022, **8**, eabn0523. doi:10.1126/sciadv.abn0523

# Towards the DEPFET 1 megapixel camera

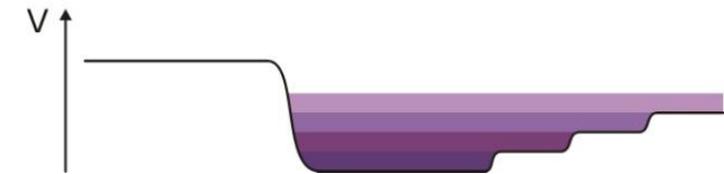
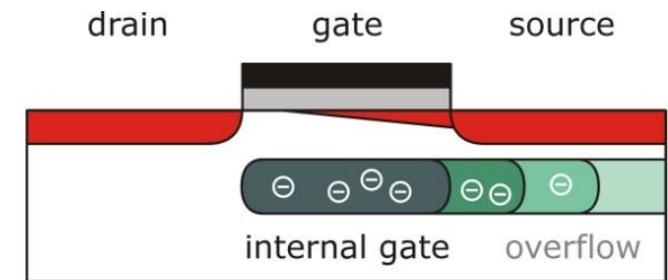
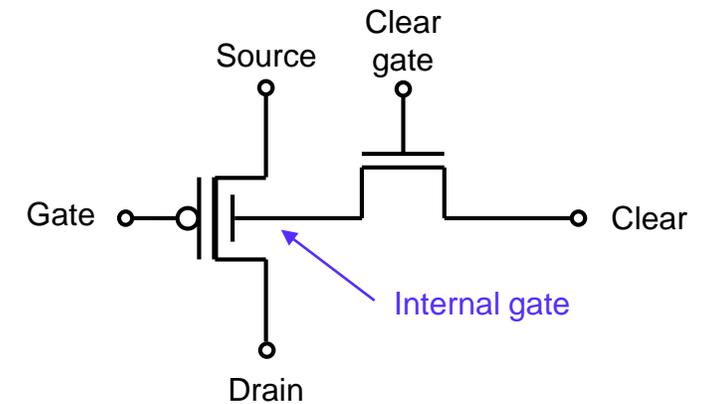
- In the second DSSC camera the MiniSDD sensors will be replaced by DEPFET arrays
  - Fully compatible ladder electronics, **additional components** installed for sensor operation
  - ASIC includes DEPFET FE
  - Produced by PNSensor
- DEPFETs are active pixels that provide a non linear response**
  - Low noise for single photon detection
  - High dynamic range**
- The DEPFET arrays are **compatible with the existing DSSC system**
- A maximum signal  $> 10^4$  ph / pixel is achievable for  $E \geq 800$  eV, assuming an 8-bit ADC and single photon detection capability**
- Common-source configuration,  $I_{DRAIN}$  readout



MiniSDD with passive collecting anode



DEPFET Active Pixel



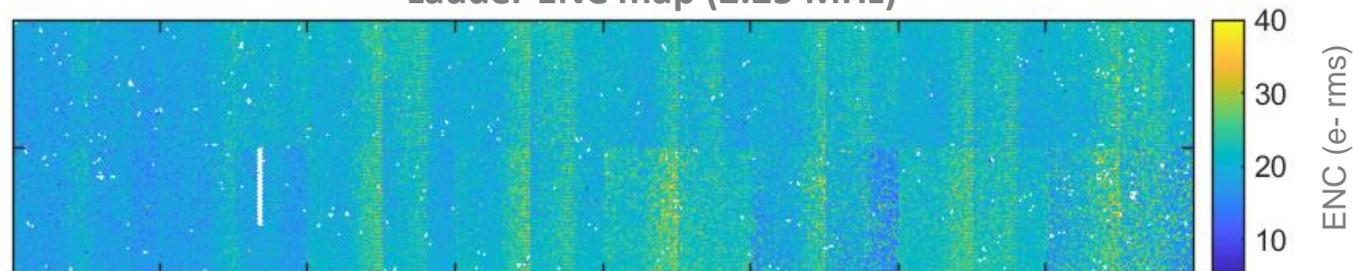
Lechner, P.; et al. DEPFET active pixel sensor with non-linear amplification, 2011 IEEE Nuclear Science Symposium Conference Record, 2011, pp. 563-568, doi:10.1109/NSSMIC.2011.6154112.

Aschauer, S.; et al. First Results on DEPFET Active Pixel Sensors Fabricated in a CMOS Foundry - a Promising Approach for New Detector Development and Scientific Instrumentation. *J. Inst.* 2017, 12, P11013–P11013. doi:10.1088/1748-0221/12/11/p11013

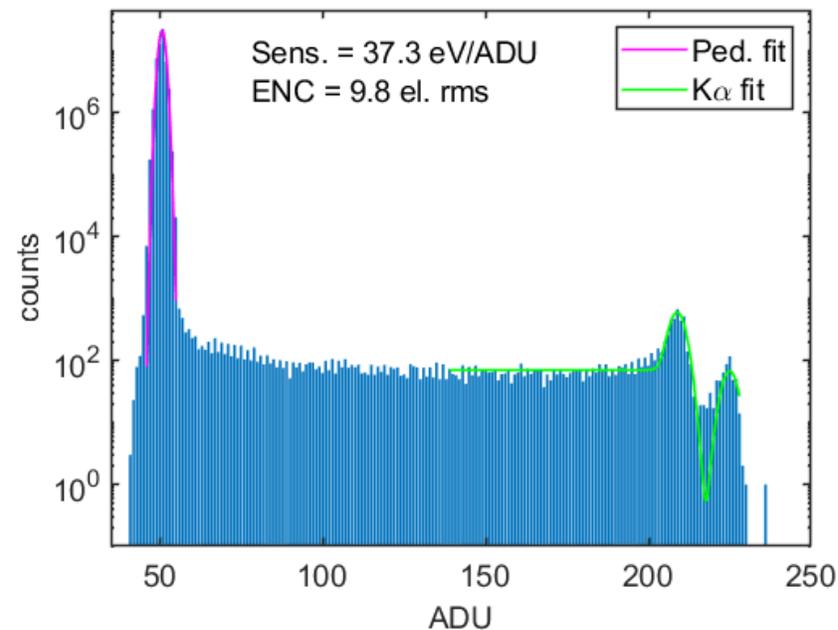
## 1<sup>st</sup> prototype characterization in the linear range

- 100  $\mu\text{A}/\text{pixel}$  average DEPFET-bias current
- ENC 20.72 e- rms with  $T_{\text{int}} = 50$  ns (2.25 MHz), 200 eV/ADU
- Down to 9.8 e- rms with  $T_{\text{int}} = 300$  ns (1.125 MHz operation), 37.3 eV/ADU
- Near room-temperature conditions

Ladder ENC map (2.25 MHz)



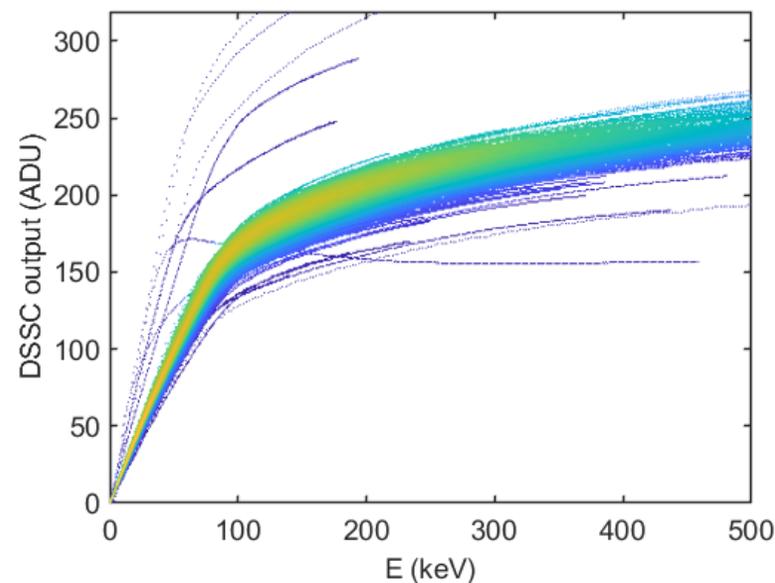
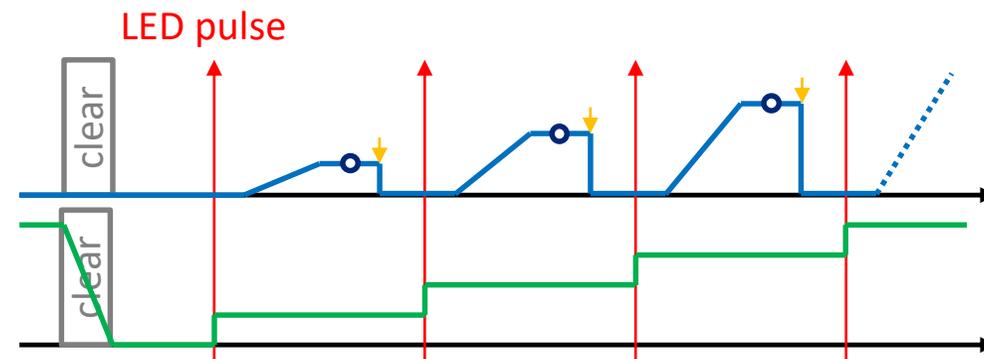
Calibration with  $^{55}\text{Fe}$  (1.125 MHz)



## Non linear characteristics evaluation

- 150 nm thick Al layer on entrance window
- laser pulser: 905 nm, 25 W
- Integrating charge into DEPFET internal gate, no clear between acquisition cycles
- Curve scan with 400 pulses in single integration mode
- 50 ns integration time
- ✓ Estimated **dynamic range** with 8 bits:
  - ~1000 ph @ 500 eV/ADU
  - ~9000 ph @ 1000 eV/ADU

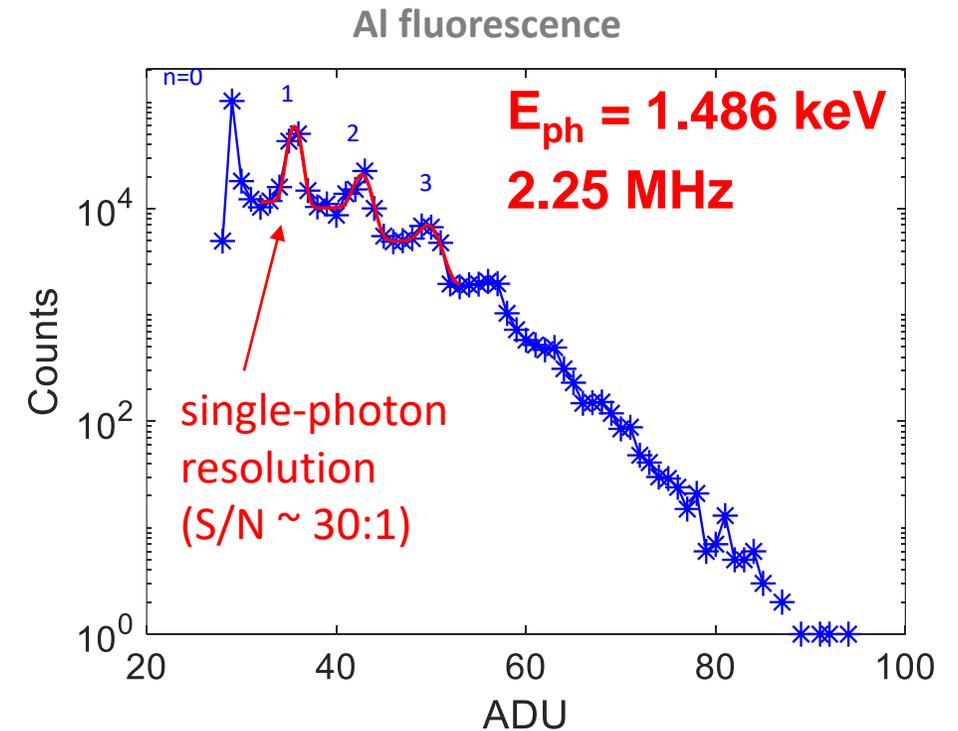
— DEPFET signal current    ● ADC sampling point  
 — Filter output            ↓ FE reset



1<sup>st</sup> kink Energy:  
 $80.6 \pm 5.4$  keV  
 Gain (linear):  
 473 eV/ADU  
 DR (@ 473eV ph):  
 > 1000 ph

## 1<sup>st</sup> prototype characterization at Small Quantum System (SQS) Instrument @ EuXFEL

- 50 ns integration time, 2.25 MHz operation (beam at 1.1MHz)
- Al fluorescence (1.486 keV)
- Single photon resolution with S/N ~ 30
- Near room temperature operation



- The first 4.5 MHz - 1 M-Pixel miniSDD-based DSSC camera has been completed and successfully installed at the Spectroscopy and Coherent scattering (SCS) scientific instrument of the European XFEL
- The performance figures of the detector system are in excellent agreement with expectations and confirm the results obtained on the prototype module
- High number of exp. since 2019, with two paper published on high-ranking journals and others in preparation
- The second 1-Mpixel camera will be based on CMOS-DEPFET active pixel sensors that allow single photon detection and high dynamic range simultaneously. The camera will be available at the end of this year (2022)
- First operation of a CMOS-DEPFET ladder in lab-test conditions confirms the excellent performances of the technology: three times better noise w.r.t. miniSDD and  $> 35$  times better DR at 1 keV/photons while keeping single photon resolution
- ENC can be as low as to 9.8 e- rms at 1.1 MHz